T2096

NPN SILICON TRANSISTOR

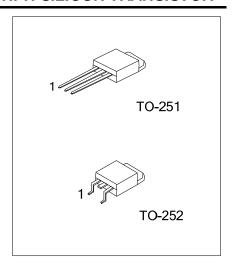
HIGH VOLTAGE TRANSISTOR

■ DESCRIPTION

The T2096 is a NPN Silicon Planar Transistors in TO-251 package. It is intended for high voltage, switching power supply and industrial applications.

■ FEATURES

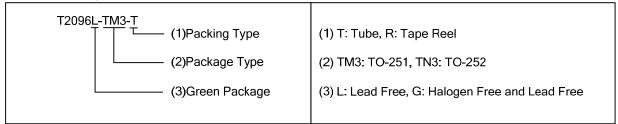
- * Pb-free package is available
- * Collector-Emitter voltage: V_{CEO} = 400V
- * Pulse collector current to 4A



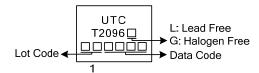
ORDERING INFORMATION

Ordering Number		Dookogo	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
T2096L-TM3-T	T2096G-TM3-T	TO-251	В	С	E	Tube	
T2096L-TN3-R	T2096G-TN3-R	TO-252	В	С	Е	Tape Reel	

Note: Pin Assignment: G: Gate D: Drain S: Source



■ MARKING



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■ **ABSOLUATE MAXIUM RATINGS** (T_A=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT	
Collector-Base Voltage		V_{CBO}	800	V	
Collector-Emitter Voltage		V _{CES}	800	V	
Collector-Emitter Voltage		$V_{\sf CEO}$	400	V	
Emitter-Base Voltage		V_{EBO}	8	V	
Base Current		Ι _Β	1	Α	
DC Collector Current		Ic	2	Α	
Pulse Collector Current (Note 2)		I _{CP}	4	Α	
Collector Dissination	T _A =25°C	В	1	W	
Collector Dissipation	T _C =25°C	Pc	15		
Junction Temperature		T_J	150	°C	
Storage Temperature		T _{STG}	-55 ~ +150	°C	

Note:1.Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

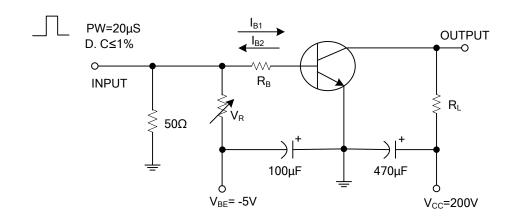
■ **ELECTRICAL CHARACTERISTICS** (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV _{CBO}	$I_C = 1mA$, $I_E = 0$	800			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C =5mA, R _{BE} =∞	400			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E = 1 \text{mA}, I_C = 0$	8			V
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	I _C =1A, I _B =0.2A			0.8	V
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	I _C =1A, I _B =0.2A			1.5	V
Collector Cutoff Current	I _{CBO}	V _{CB} =400V, I _E =0			10	μΑ
Emitter Cutoff Current	I _{EBO}	$V_{EB} = 5V$, $I_C = 0$			10	μΑ
DC Current Gain	h _{FE 1}	V_{CE} =5V, I_{C} =1mA	45			
DC Current Gain	h _{FE 2}	$V_{CE} = 5V, I_{C} = 0.2A$	120		180	
Current Gain-Bandwidth Product	f _T	$V_{CE} = 10V, I_{C} = 0.2A$		20		MHz
Output Capacitance	Cob	V _{CB} =10V, f=1MHz		20		pF
Turn-on Time	t _{ON}	I _C =1.0A, I _{B1} =0.05A			0.5	μs
Storage Time	t _{STG}	$I_{B2} = -0.5A, R_L = 200\Omega$			2.5	μs
Fall Time	t _F	V _{CC} =200V			0.3	μs



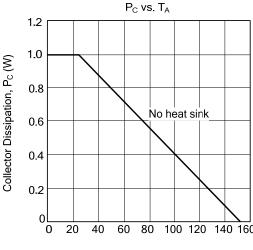
^{2.} Pulse Test: Pulse Width ≤300µS, Duty Cycle≤10%

■ SWITCHING TIME TEST CIRCUIT

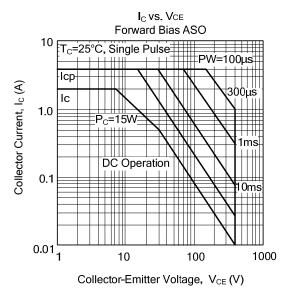


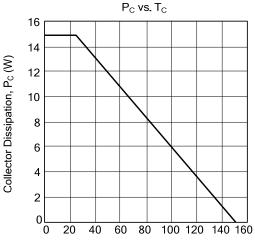


■ TYPICAL CHARACTERISTICS

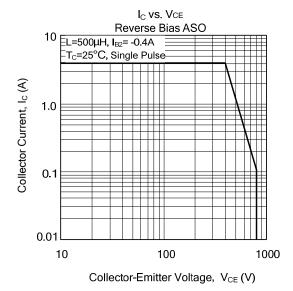








Case Temperature, T_C (°C)



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